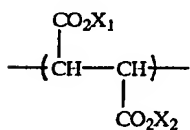


AMENDMENTS TO THE CLAIMS:

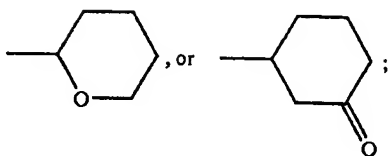
Please amend the claims as follows:

1-10. (Cancelled)

11. (Withdrawn) A radiation sensitive material comprising: a copolymer including a unit structure expressed by



(where X_1 and X_2 represent $-\text{C}(\text{CH}_3)_2\text{R}_1$,



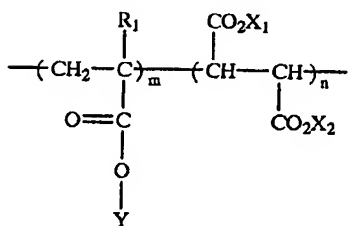
and

R₁ represents alkyl group); and

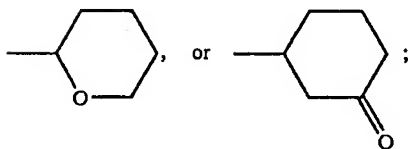
a unit structure generating an alkali soluble group in the presence of an acid; and

a substance generating acid by application of radiation.

12. (Withdrawn) A radiation sensitive material comprising: a copolymer expressed by a general formula



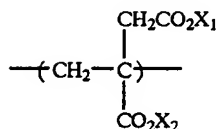
(where X₁ and X₂ represent -C(CH₃)₂R₂,



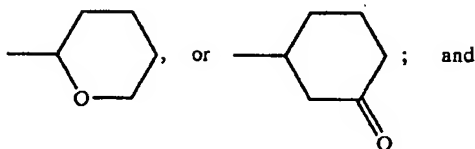
Y represents alicyclic group; R₁ represent CH₃ or H; and R₂ represents alkyl group); and

a substance generating an acid by application of radiation.

13. (Withdrawn) A radiation sensitive material comprising: a copolymer including a unit structure expressed by



(where X_1 and X_2 represent $-\text{C}(\text{CH}_3)_2\text{R}_1$,

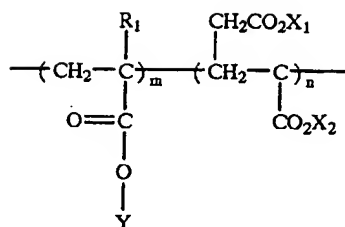


R_1 represents alkyl group); and

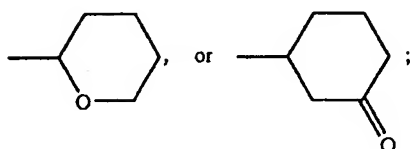
a unit structure generating an alkali soluble group in the presence of an acid; and

a substance generating an acid by application of radiation.

14. (Withdrawn) A radiation sensitive material comprising: a copolymer expressed by a general formula



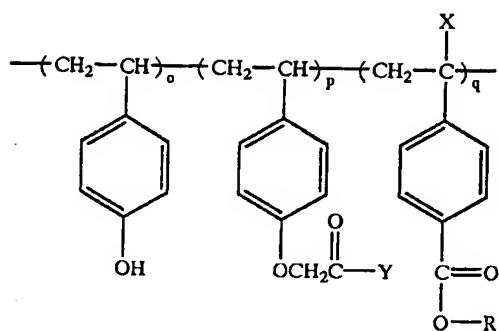
(where X_1 and X_2 represent $\text{---C}(\text{CH}_3)_2\text{R}_2$,



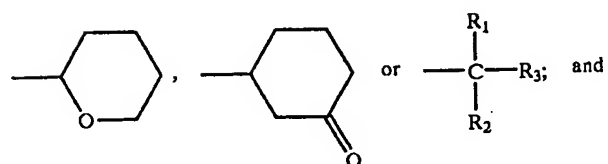
Y represents alicyclic group; R_1 represent CH_3 or H ; and R_2 represents alkyl group); and a substance generating an acid by application of radiation.

15-19. (Cancelled)

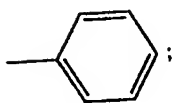
20. (Withdrawn) A radiation sensitive material comprising a terpolymer expressed by a general formula



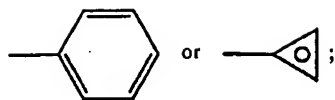
(where X represents H or CH₃; R represents



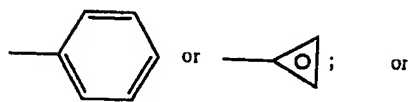
R₁ and R₂ represent H, R₃ represents



R₁ represents CH₃, R₂ represents H, R₃ represents



R_1 and R_2 represent CH_3 , R_3 represents



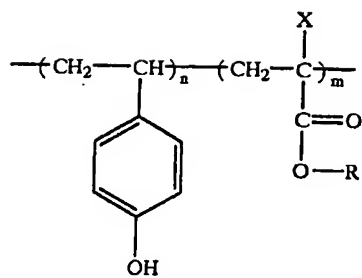
R_1 , R_2 and R_3 represent CH_3); and

a substance generating an acid by application of radiation

21. (Withdrawn) A radiation sensitive material comprising:

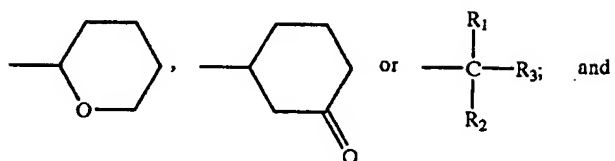
a resist containing a hydrophilic group; and a hydrophobic compound.

22. (Withdrawn) A radiation sensitive material according to claim 21, wherein the resist containing a hydrophilic group is a copolymer expressed by a general formula

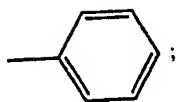


(where X represents H or CH₃;

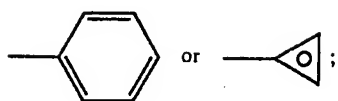
R represents



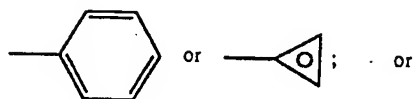
and R₁ and R₂ represent H, R₃ represents



R₁ represents CH₃, R₂ represents H, R₃ represents



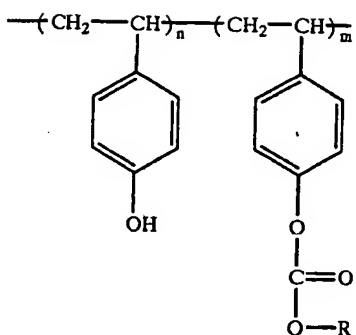
R₁ and R₂ represent CH₃, R₃ represents



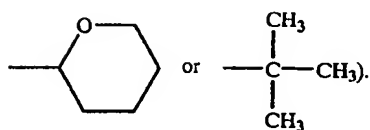
R₁, R₂ and R₃ represent CH₃).

23. (Withdrawn) A radiation sensitive material according to claim 22, wherein vinylphenol of the resist containing hydrophilic groups is contained by 50-70 mol %.

24. (Withdrawn) A radiation sensitive material according to claim 21, wherein the resist containing hydrophilic groups is a copolymer expressed by a general formula

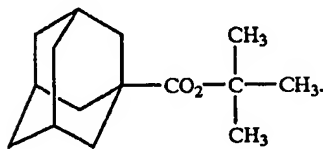


(where R represents

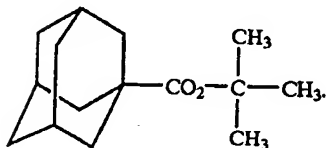


25. (Withdrawn) A radiation sensitive material according to claim 24, wherein vinylphenol in the resist containing the hydrophilic group is contained 60-80 mol %.

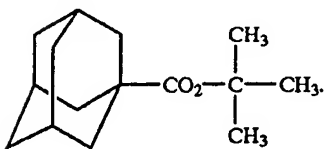
26. (Withdrawn) A radiation sensitive material according to claim 21, wherein the hydrophobic compound is expressed by



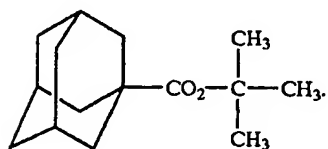
27. (Withdrawn) radiation sensitive material according to claim 22, wherein the hydrophobic compound is expressed by



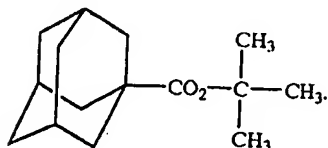
28. (Withdrawn) A radiation sensitive material according to claim 23, wherein the hydrophobic compound is expressed by



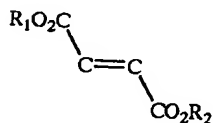
29. (Withdrawn) A radiation sensitive material according to claim 24, wherein the hydrophobic compound is expressed by



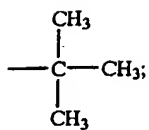
30. (Withdrawn) A radiation sensitive material according to claim 25, wherein the hydrophobic compound is expressed by



31. (Withdrawn) A radiation sensitive material according to claim 21, wherein the hydrophobic compound is expressed by a general formula

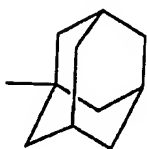


(where R₁ and R₂ represent

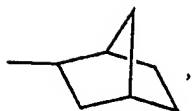


or

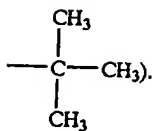
R₁ represents



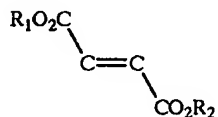
or



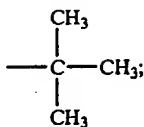
R₂ represents



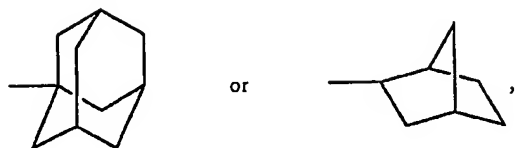
32. (Withdrawn) A radiation sensitive material according to claim 22, wherein the hydrophobic compound is expressed by a general formula



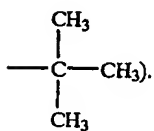
(where R₁ and R₂ represent



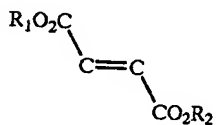
or R₁ represents



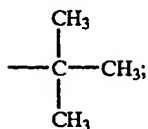
R₂ represents



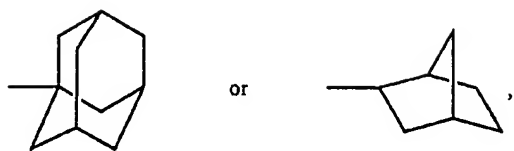
33. (Withdrawn) A radiation sensitive material according to claim 23, wherein the hydrophobic compound is expressed by a general formula



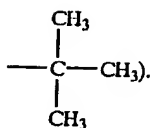
(where R₁ and R₂ represent



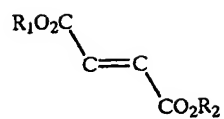
or R₁ represents



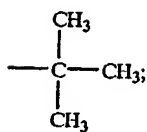
R₂ represents



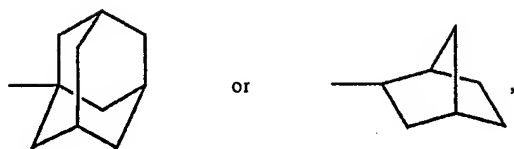
34. (Withdrawn) A radiation sensitive material according to claim 24, wherein the hydrophobic compound is expressed by a general formula



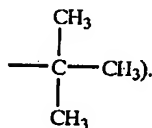
(where R_1 and R_2 represent



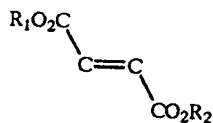
or R_1 represents



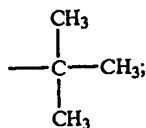
R₂ represents



35. (Withdrawn) A radiation sensitive material according to claim 25, wherein the hydrophobic compound is expressed by a general formula

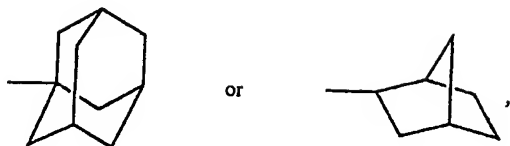


(where R₁ and R₂ represent

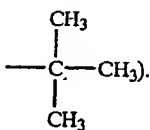


or

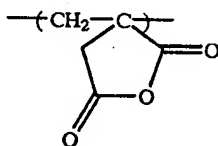
R₁ represents



R₂ represents



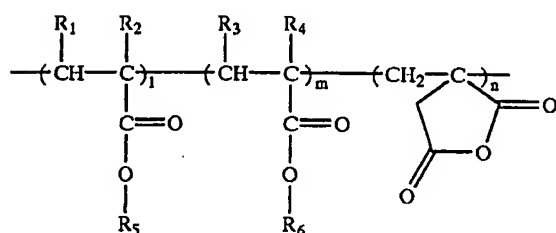
36. (Currently Amended) A radiation sensitive material comprising: a copolymer including itaconic anhydride which is expressed by



a unit structure including an alicyclic structure or an aromatic structure; and

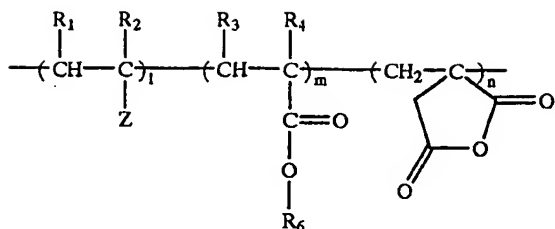
a polymer as a unit structure which generates an alkali soluble group in the presence of an acid; and
a substance generating an acid by application of radiation.

37. (Currently Amended) A radiation sensitive material according to claim 36, wherein the copolymer is expressed by a general formula



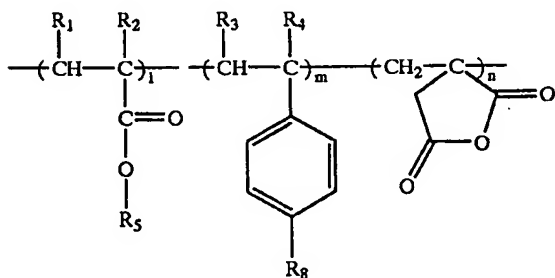
(where l, m and n represent 0 ≤ l ≤ 60 mol %, 10-95 mol %, 5-50 mol % respectively; R₁, R₂, R₃ and R₄ represent H, halogen, C₁₋₄ alkyl group, C₁₋₄ substituted alkyl group, nitrile group, -(CH₂)_nCOOR₅(n=0-1) or -(CH₂)_nCOOR₆(n=0-1); R₅ represents C₄₋₅ alkyl group, C₄₋₅ substituted alkyl group, alicyclic group, substituted alicyclic group, aromatic group or substituted aromatic group; and R₆ represents t-butyl group, t-amyl group, dimethylbenzyl group, tetrahydropyranyl group or 3-oxocyclohexyl group).

38. (Currently Amended) A radiation sensitive material according to claim 36, wherein the copolymer is expressed by



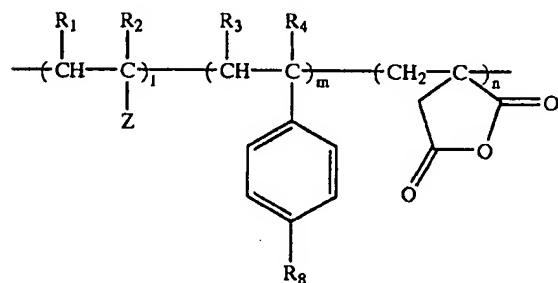
(where l, m and n represent 1-95 mol %, 10-95 mol % and 5-50 mol %; Z represents benzene ring, substituted benzene ring, ~~nitrile group~~, -OR₇, -COR₇ or -OCOR₇; R₁, R₂, R₃ and R₄ represent H, halogen, C₁₋₄ alkyl group, C₁₋₄ substituted alkyl group, nitrile group, -C(CH₂)_nCOOR₅(n=0-1), or -(CH₂)_nCOOR₆(n=0-1); R₆ represents t-butyl group, t-amyl group, dimethylbenzyl group, tetrahydropyranyl group or 3-oxocyclohexyl group; R₇ represents ~~C₄₋₅ alkyl group, C₄₋₅ substituted alkyl group~~, alicyclic group, substituted alicyclic group, aromatic group or substituted aromatic group) ; and R₅ represents alicyclic group, substituted alicyclic group, aromatic group or substituted aromatic group.

39. (Currently Amended) A radiation sensitive material according to claim 36, wherein the copolymer is expressed by a general formula .



(where l, m and n represent $0 \leq l \leq 95$ mol %, $1 \leq m \leq 95$ mol % and $5 \leq n \leq 50$ mol %; R_1 , R_2 , R_3 and R_4 represent H, halogen, C_{1-4} alkyl group, C_{1-4} substituted alkyl group, nitrile group, $-(CH_2)_nCOOR_5$ ($n=0-1$) or $-(CH_2)COOR_6$ ($n=0-1$); R_5 represents ~~C_{4-5} alkyl group, C_{4-5} substituted alkyl group~~, alicyclic group, substituted alicyclic group, aromatic group or substituted aromatic group; R_6 represents t-butyl group, t-amyl group, dimethylbenzyl group, tetrahydropyranyl group or 3-oxocyclohexyl group; and R_8 represents -OtBu, -OCOOtBu or -COOt-Amyl).

40. (Currently Amended) A radiation sensitive material according to claim 36, wherein the copolymer is expressed by a general formula



(where l, m and n represent $0 \leq l \leq 95$ mol %, $1 \leq m \leq 95$ mol % and $5 \leq n \leq 50$ mol %; Z represents benzene ring, substituted benzene ring, ~~nitrile group~~, OR_7 , $-COR_7$ or $-OCOR_7$; R_1 , R_2 , R_3 and R_4 represent H, halogen, C_{1-4} alkyl group, C_{1-4} , -4 substituted alkyl group, nitrile group, $-(CH_2)_nCOOR_5$ ($n=0-1$) or $-(CH_2)_nCOOR_6$ ($n=0-1$); R_5 represents alicyclic group, substituted alicyclic group, aromatic group or substituted aromatic group; R_6 represents t-butyl group, t-amyl group, dimethylbenzyl group, tetrahydropyranyl group or 3-oxocyclohexyl group; R_7 represents alicyclic group, substituted alicyclic group, aromatic group or substituted aromatic group; and R_8 represents -OtBu,

-OCOOtBu, or -COOt-Amyl).

41. (Original) A radiation sensitive material according to claim 36, wherein the copolymer includes the unit structure including the itaconic anhydride by 5-50 mol %.

42. (Original) A radiation sensitive material according to claim 37, wherein the copolymer includes the unit structure including the itaconic anhydride by 5-50 mol %.

43. (Original) A radiation sensitive material according to claim 38, wherein the copolymer includes the unit structure including the itaconic anhydride by 5-50 mol %.

44. (Original) A radiation sensitive material according to claim 39, wherein the copolymer includes the unit structure including the itaconic anhydride by 5-50 mol %.

45. (Original) A radiation sensitive material according to claim 40, wherein the copolymer includes the unit structure including the itaconic anhydride by 5-50 mol %.

46-50. (Cancelled)

51. (Withdrawn) A method for forming a pattern comprising the steps of: preparing a resist of a radiation sensitive material according to claim 11; applying the resist to a substrate to be processed; prebaking the substrate and then selectively exposing the

resist on the substrate to radiation; and postbaking the substrate, and then developing the resist on the substrate to form the pattern.

52. (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material according to claim 12;
applying the resist to a substrate to be processed;
prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and
postbaking the substrate, and then developing the resist on the substrate to form the pattern.

53. (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material according to claim 13;
applying the resist to a substrate to be processed;
prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and
postbaking the substrate, and then developing the resist on the substrate to form the pattern.

54. (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material according to claim 14;

applying the resist to a substrate to be processed; prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and postbaking the substrate, and then developing the resist on the substrate to form the pattern.

55. (Cancelled)

56 (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material according to claim 20;
applying the resist to a substrate to be processed; prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and
postbaking the substrate, and then developing the resist on the substrate to form the pattern.

57. (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material according to claim 21;
applying the resist to a substrate to be processed;
prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and
postbaking the substrate, and then developing the resist on the substrate to form the pattern.

58. (Original) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material according to claim 36;

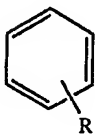
applying the resist to a substrate to be processed; prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and postbaking the substrate, and then developing the resist on the substrate to form the pattern.

59. (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a radiation sensitive material;
applying the resist to a substrate to be processed;
prebaking the substrate and then selectively exposing the resist on the substrate to radiation; and postbaking the substrate, and then developing the resist on the substrate by a developer being a mixed liquid of an organic alkaline aqueous solution and isopropyl alcohol to form the pattern.

60. (Withdrawn) A method for forming a pattern according to claim 59, wherein the developer contains the isopropyl alcohol by 5-95 vol %.

61. (Withdrawn) A method for forming a pattern comprising the steps of:
preparing a resist of a polymer containing an acrylic ester unit, having an alicyclic group at an ester unit, or a methacrylic ester unit, having an alicyclic group at an ester unit, and an acrylic ester unit having a polar structure at an ester unit or a methacrylic ester unit having a polar structure at an ester unit;
coating a substrate to be processed with the resist, and prebaking the substrate to be processed;

applying onto the resist a protecting film of a hydrocarbon-based polymer, which is transparent to far ultraviolet rays, and heating the same;
selectively exposing radiation to the resist on the substrate to be processed;
postbaking the substrate to be processed;
stripping the protecting film; and
developing the resist on the substrate to be processed to form a desired resist pattern, an application solvent for the hydrocarbon-based polymer of the protecting film being a non-aromatic hydrocarbon, or an aromatic hydrocarbon expressed by a general formula



(where R represents an alkyl group with 3 or more carbon atoms).

62. (Original) A method for forming a pattern comprising the steps of:
forming a resist of a radiation sensitive material according to claims 36; coating a substrate-to-be-processed with the resist, and prebaking the substrate to be processed;
applying a protecting film of a hydrocarbon polymer, which is transparent to far ultraviolet rays, and heating the same;
selectively exposing radiation to the resist on the substrate to be processed, and
postbaking the substrate to be processed; and

stripping the protecting film, and developing the resist on the substrate to be processed to form a desired resist pattern.

63. (Withdrawn) A method for forming a pattern according to claim 61, wherein an application solvent for the hydrocarbon polymer for the protecting film is limonene, 1,5-cyclooctadiene, 1-decene, t-butylcyclohexane, p-cymene or dodecylbenzene.

64. (Original) A method for forming a pattern according to claim 62, wherein an application solvent for the hydrocarbon polymer for the protecting film is limonene, 1,5-cyclooctadiene, 1-decene, t-butylcyclohexane, p-cymene or dodecylbenzene.

65. (Withdrawn) A method for forming a pattern according to claim 61, wherein the hydrocarbon polymer is an olefine polymer or a diene polymer.

66. (Original) A method for forming a pattern according to claim 62, wherein the hydrocarbon polymer is an olefine polymer or a diene polymer.

67. (Withdrawn) A method for forming a pattern according to claim 63, wherein the hydrocarbon polymer is an olefine polymer or a diene polymer.

68. (Original) A method for forming a pattern according to claim 64, wherein the hydrocarbon polymer is an olefine polymer or a diene polymer.

69. (Original) A method for forming a pattern according to claim 62, wherein the substance having a polar-structure is ketone, alcohol, ether, ester, carbonic acid, an acid anhydride, or any one of these substances having a part of the atoms of a polar structure.

70. (Cancelled)

71. (Withdrawn) A semiconductor fabrication method comprising a step of patterning the resist by a method for forming a pattern according to claim 61.